

## RBV800 - RBV810

**PRV : 50 - 1000 Volts**

**Io : 8.0 Amperes**

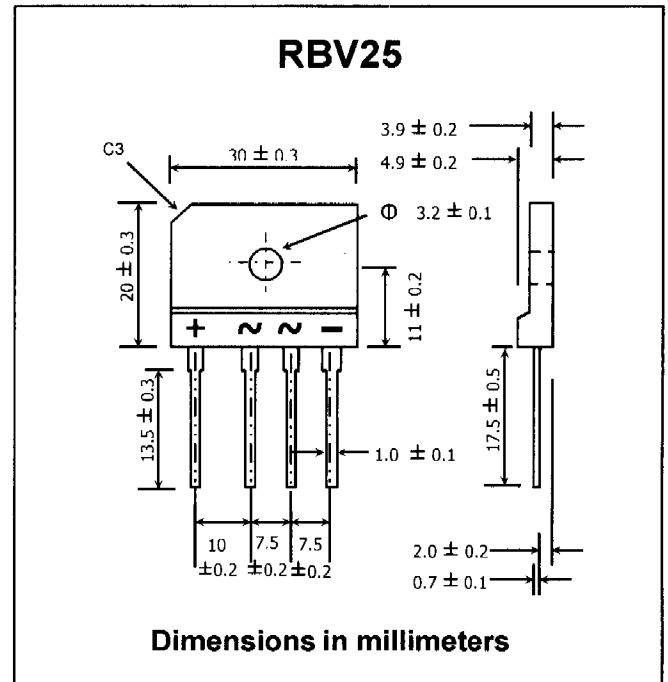
### FEATURES :

- \* High current capability
- \* High surge current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* Rated isolation-voltage 2000 V<sub>AC</sub>
- \* Ideal for printed circuit board
- \* Very good heat dissipation
- \* Pb / RoHS Free

### MECHANICAL DATA :

- \* Case : Reliable low cost construction utilizing molded plastic technique
- \* Epoxy : UL94V-0 rate flame retardant
- \* Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Polarity symbols marked on case
- \* Mounting position : Any
- \* Weight : 7.97 grams ( Approximaly )

## SILICON BRIDGE RECTIFIERS



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

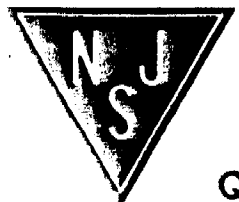
Rating at 25 °C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

RATING	SYMBOL	RBV 800	RBV 801	RBV 802	RBV 804	RBV 806	RBV 808	RBV 810	UNIT
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Maximum Average Forward Current T <sub>c</sub> = 55°C	I <sub>F(AV)</sub>	8.0							A
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	300							A
Current Squared Time at t < 8.3 ms.	I <sup>2</sup> t	160							A <sup>2</sup> S
Maximum Forward Voltage per Diode at I <sub>F</sub> = 4.0 A	V <sub>F</sub>	1.0							V
Maximum DC Reverse Current T <sub>a</sub> = 25 °C at Rated DC Blocking Voltage T <sub>a</sub> = 100 °C	I <sub>R</sub>	10							μA
	I <sub>R(H)</sub>	200							μA
Typical Thermal Resistance (Note 1)	R <sub>θJC</sub>	2.5							°C/W
Operating Junction Temperature Range	T <sub>J</sub>	- 40 to + 150							°C
Storage Temperature Range	T <sub>STG</sub>	- 40 to + 150							°C

#### Notes :

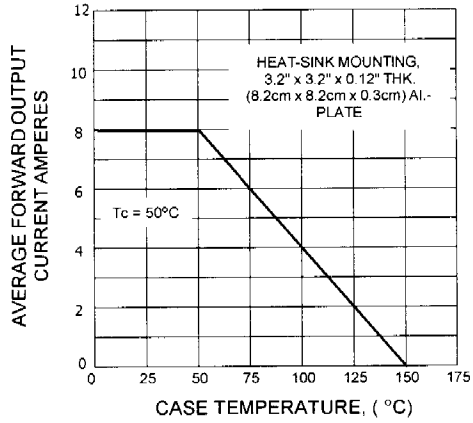
1. Thermal Resistance from junction to case with units mounted on a 3.2"x3.2"x0.12" THK (8.2cm.x8.2cm.x0.3cm.) Al. Plate. heatsink.

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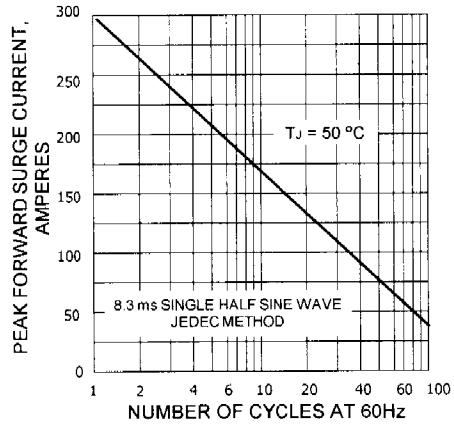


## RATING AND CHARACTERISTIC CURVES ( RBV800 - RBV810 )

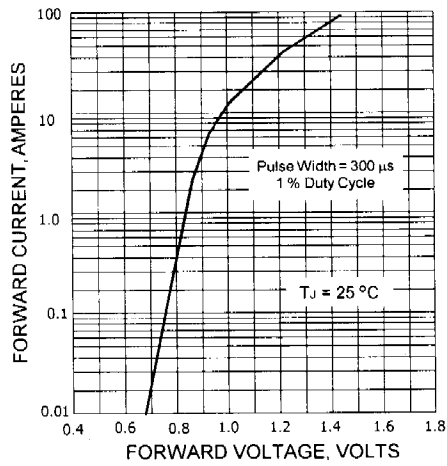
**FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE**

